

Amendments to the Specification:

Please replace the title of the application with the following title:

SEMICONDUCTOR DEVICE WITH EXPOSED ELECTRODES

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device, comprising:  
a first substrate formed of an insulating material having at least one through hole;  
a semiconductor element secured to a desired position of a conductive pattern formed on a first main surface of said the first substrate;  
~~a metal wire for electrically connecting an electrode pad of said semiconductor element to said desired conductive pattern;~~  
a plurality of electrodes for external connection on a second main surface of said the first substrate located opposite to the first main surface of said the first substrate that is electrically connected to said the desired conductive pattern via said the through hole;  
a resin mold formed so as to cover, at least, the main surfaces of said the first substrate, wherein the semiconductor device is characterized in that a second substrate formed of an insulating material having approximately the a same coefficient of linear expansion as said the first substrate is adhered to the second main surface of said the first substrate so that, at least, said the electrodes ~~for external connection~~ are exposed.
  
2. (Currently Amended) The semiconductor device according to Claim 1, characterized in that said the second substrate is adhered to said the first substrate so that, at least, the sides of

said the electrodes ~~for external connection~~ located in the vicinity of the outer sides of the second main surface of said the first substrate are exposed from ~~said~~ the outer sides.

3. (Currently Amended) The semiconductor device according to Claim 1, characterized in that ~~said~~ the second substrate separates ~~from each other~~ ~~said~~ the electrodes ~~for external connection on the second main surface of said first substrate~~ from each other so that the electrodes exist independently in separate regions.

4. (Currently Amended) The semiconductor device according to Claim 2, characterized in that ~~said~~ the second substrate is thicker than ~~said~~ the electrodes for external connection.

5. (Currently Amended) The semiconductor device according to Claim 2, characterized in that ~~said~~ the electrodes ~~for external connection~~ are plated with gold.

6. (Currently Amended) The semiconductor device according to Claim 2, characterized in that ~~said~~ the first and second substrates are ceramic substrates.

7. (Currently Amended) The semiconductor device according to Claim 2, characterized in that ~~said~~ the second substrate separates ~~from each other~~ ~~said~~ the electrodes ~~for external connection on the second main surface of said the first substrate~~ from each other so that the electrodes exist independently in separate regions.

8. (Currently Amended) The semiconductor device according to Claim 3, characterized in that ~~said~~ the second substrate is thicker than ~~said~~ the electrodes ~~for external connection~~.

9. (Currently Amended) The semiconductor device according to Claim 3, characterized in that ~~said~~ the electrodes ~~for external connection~~ are plated with gold.

10. (Currently Amended) The semiconductor device according to Claim 3, characterized in that ~~said~~ the first and second substrates are ceramic substrates.

11. (New) The semiconductor device according to claim 1, comprising a metal wire to electrically connect an electrode pad of the semiconductor element to the desired conductive pattern.

12. (New) A method for forming a semiconductor device, comprising:  
adhering a second substrate to a second surface of a first substrate;  
subsequently mounting a semiconductor element on a first surface of the first substrate;  
and

electrically coupling the semiconductor element to one or more electrodes on the second surface of the first substrate,  
wherein the electrodes are exposed.

13. (New) The method of claim 12, wherein a thickness of the second substrate is greater than a thickness of the electrode.

14. (New) The method of claim 12, wherein a coefficient of expansion of the first substrate and a coefficient of expansion of the second substrate are substantially equal.

Applicant : Takayuki Tani et al.  
Serial No. : 10/650,433  
Filed : August 28, 2003  
Page : 5 of 9

Attorney's Docket No.: 14225-020001 / F1030443US00

Amendments to the Drawings:

The attached replacement sheets drawings include changes to Figs. 6, 7A, 7B and 7C and replace the original sheets including Fig. 5, 6, 7A, 7B and 7C.

In Figures 6, 7A, 7B and 7C: added the legend "Prior Art"

Attachments following last page of this Amendment:

Replacement Sheet (2 pages)